

## ESDA25B1

## Application Specific Discretes A.S.D.<sup>TM</sup>

# TRANSIL<sup>TM</sup> ARRAY FOR ESD PROTECTION

#### **APPLICATIONS**

Where transient overvoltage protection in ESD sensitive equipment is required, such as:

- COMPUTER
- PRINTERS
- COMMUNICATION SYSTEMS

It is particulary recommended for RS232 I/O port protection where the line interface withstands only 2 kV ESD surges.

## **FEATURES**

- 6 BIDIRECTIONAL TRANSIL™ FUNCTIONS
- VERY LOW CAPACITANCE : C= 20 pF @ V<sub>RM</sub>
- 150 W peak pulse power (8/20 µs)

## **DESCRIPTION**

The ESDA25B1 is a monolithic voltage suppressor designed to protect components which are connected to data and transmission lines against EDS.

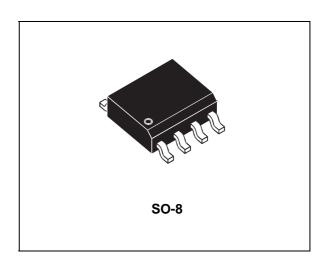
## **BENEFITS**

High ESD protection level : up to 25 kV High integration Suitable for high density boards

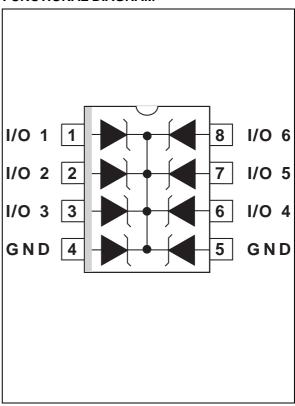
## **COMPLIES WITH THE FOLLOWING STANDARDS:**

IEC 1000-4-2: level 4

MIL STD 883C-Method 3015-6 : class 3 (human body model)



## **FUNCTIONAL DIAGRAM**



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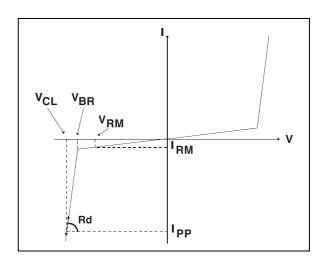
## ESDA25B1

## ABSOLUTE MAXIMUM RATINGS (Tamb = 25°C)

Symbol	Parameter	Value	Unit
V <sub>PP</sub>	Electrostatic discharge MIL STD 883C - Method 3015-6	25	kV
P <sub>PP</sub>	Peak pulse power (8/20μs)	150	W
T <sub>stg</sub> T <sub>j</sub>	Storage temperature range Maximum junction temperature	- 55 to + 150 125	္ခိုင္
TL	Maximum lead temperature for soldering during 10s	260	°C

## **ELECTRICAL CHARACTERISTICS** (T<sub>amb</sub> = 25°C)

Symbol	Parameter				
VRM	Stand-off voltage				
$V_{BR}$	Breakdown voltage				
VcL	Clamping voltage				
I <sub>RM</sub>	Leakage current				
l <sub>PP</sub>	Peak pulse current				
ατ	Voltage temperature coefficient				
С	Capacitance				
Rd	Dynamic resistance				



Types	V <sub>BR</sub> @		I <sub>R</sub>	I <sub>RM</sub> @	V <sub>RM</sub>	Rd	αΤ	С
	min.	max.		max.		typ.	max.	typ.
	note 1			note 1		note 2	note 3	0V bias
	V	V	mA	μΑ	V	Ω	10 <sup>-4</sup> /°C	pF
ESDA25B1	25	30	1	2	24	1.5	9.7	15

 $\begin{array}{l} \textbf{note 1}: \mbox{Between any I/O pin and Groung} \\ \textbf{note 2}: \mbox{Square pulse}, \mbox{ Ipp} = 25\mbox{A}, \mbox{tp=2.5}\mbox{\mus}. \\ \textbf{note 3}: \mbox{ } \Delta \mbox{ } V_{BR} = \mbox{ } \alpha \mbox{T}^* \mbox{ } (\mbox{Tamb -}25^{\circ}\mbox{C}) \mbox{ }^* \mbox{ } V_{BR} \mbox{ } (25^{\circ}\mbox{C}) \end{array}$ 

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## **CALCULATION OF THE CLAMPING VOLTAGE**

## **USE OF THE DYNAMIC RESISTANCE**

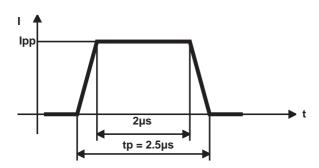
The ESDA family has been designed to clamp fast spikes like ESD. Generally the PCB designers need to calculate easily the clamping voltage  $V_{\text{CL}}$ . This is why we give the dynamic resistance in addition to the classical parameters. The voltage across the protection cell can be calculated with the following formula:

$$V_{CL} = V_{BR} + Rd I_{PP}$$

Where Ipp is the peak current through the ESDA cell.

## DYNAMIC RESISTANCE MEASUREMENT

The short duration of the ESD has led us to prefer a more adapted test wave, as below defined, to the classical 8/20µs and 10/1000µs surges.

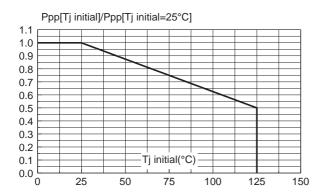


2.5µs duration measurement wave.

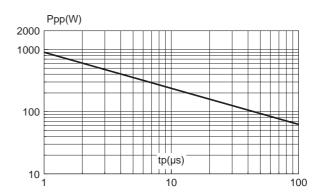
As the value of the dynamic resistance remains stable for a surge duration lower than  $20\mu s$ , the  $2.5\mu s$  rectangular surge is well adapted. In addition both rise and fall times are optimized to avoid any parasitic phenomenon during the measurement of Rd.

## ESDA25B1

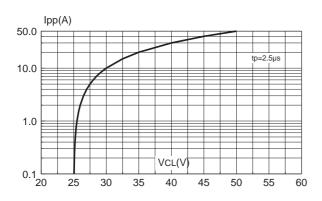
**Fig. 1**: Peak power dissipation versus initial junction temperature.



**Fig. 2 :** Peak pulse power versus exponential pulse duration (Tj initial =  $25 \, ^{\circ}$ C).



**Fig. 3** : Clamping voltage versus peak pulse current (Tj initial = 25 °C). Rectangular waveform tp =  $2.5 \,\mu s$ .



**Fig. 4** : Capacitance versus reverse applied voltage (typical values).

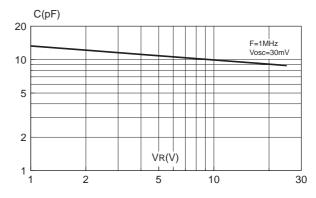
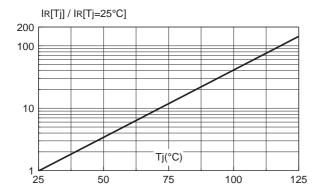
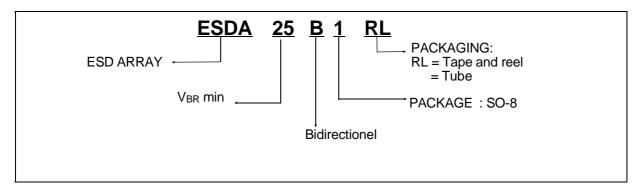


Fig. 5: Relative variation of leakage current versus junction temperature (typical values).



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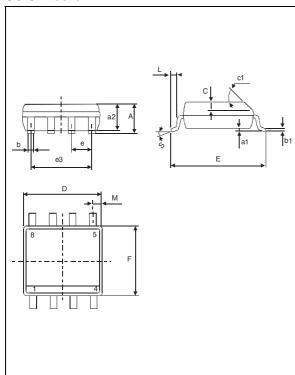
## **ORDER CODE**



MARKING: Logo, Date Code, E25B1

## **PACKAGE MECHANICAL DATA**

SO-8 Plastic



	DIMENSIONS						
REF.	Mi	illimete	ers	Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α			1.75			0.069	
a1	0.1		0.25	0.004		0.010	
a2			1.65			0.065	
a3	0.65		0.85	0.026		0.033	
b	0.35		0.48	0.014		0.019	
b1	0.19		0.25	0.007		0.010	
С	0.25		0.5	0.010		0.020	
c1			45°	(typ)			
D	4.8		5.0	0.189		0.197	
Е	5.8		6.2	0.228		0.244	
е		1.27			0.050		
e3		3.81			0.150		
F	3.8		4.0	0.15		0.157	
L	0.4		1.27	0.016		0.050	
M			0.6			0.024	
S	8° (max)						

Packaging: Preferred packaging is tape and reel.

Weight: 0.08g.

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